

Shijie Xu

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#	Paper	IF	Citations
287	Optical signature of symmetry variations and spin-valley coupling in atomically thin tungsten dichalcogenides. <i>Scientific Reports</i> , 2013 , 3, 1608	4.9	659
286	Different origins of visible luminescence in ZnO nanostructures fabricated by the chemical and evaporation methods. <i>Applied Physics Letters</i> , 2004 , 85, 1601-1603	3.4	564
285	Stress and its effect on optical properties of GaN epilayers grown on Si(111), 6H-SiC(0001), and c-plane sapphire. <i>Applied Physics Letters</i> , 2003 , 83, 677-679	3.4	321
284	Carbon-coated CdS petalous nanostructures with enhanced photostability and photocatalytic activity. <i>Angewandte Chemie - International Edition</i> , 2013 , 52, 5636-9	16.4	310
283	Luminescence characteristics of impurities-activated ZnS nanocrystals prepared in microemulsion with hydrothermal treatment. <i>Applied Physics Letters</i> , 1998 , 73, 478-480	3.4	201
282	Effects of rapid thermal annealing on structure and luminescence of self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 1998 , 72, 3335-3337	3.4	170
281	Room-temperature continuous-wave electrically injected InGaN-based laser directly grown on Si. <i>Nature Photonics</i> , 2016 , 10, 595-599	33.9	151
280	Semiconducting and electroluminescent nanowires self-assembled from organoplatinum(II) complexes. <i>Angewandte Chemie - International Edition</i> , 2008 , 47, 9895-9	16.4	150
279	Characteristics of InGaAs quantum dot infrared photodetectors. <i>Applied Physics Letters</i> , 1998 , 73, 3153-3155	3.4	140
278	Thermal redistribution of localized excitons and its effect on the luminescence band in InGaN ternary alloys. <i>Applied Physics Letters</i> , 2001 , 79, 1810-1812	3.4	130
277	Enhanced Photoluminescence and Characterization of Mn-Doped ZnS Nanocrystallites Synthesized in Microemulsion. <i>Langmuir</i> , 1997 , 13, 6427-6431	4	108
276	Carbon-Coated CdS Petalous Nanostructures with Enhanced Photostability and Photocatalytic Activity. <i>Angewandte Chemie</i> , 2013 , 125, 5746-5749	3.6	106
275	Cubic-phase GaN light-emitting diodes. <i>Applied Physics Letters</i> , 1999 , 74, 2498-2500	3.4	96
274	A model for steady-state luminescence of localized-state ensemble. <i>Europhysics Letters</i> , 2005 , 71, 994-1000	3.4	95
273	Nature and elimination of yellow-band luminescence and donor-acceptor emission of undoped GaN. <i>Applied Physics Letters</i> , 1999 , 74, 2821-2823	3.4	88
272	Characteristics of self-guided laser plasma channels generated by femtosecond laser pulses in air. <i>Physical Review E</i> , 2002 , 66, 016406	2.4	84
271	Luminescence and thermal behaviors of free and trapped excitons in cesium lead halide perovskite nanosheets. <i>Nanoscale</i> , 2018 , 10, 9949-9956	7.7	80

270	Observation of optically-active metastable defects in undoped GaN epilayers. <i>Applied Physics Letters</i> , 1998 , 72, 2451-2453	3.4	80
269	Engineering the Exciton Dissociation in Quantum-Confined 2D CsPbBr ₃ Nanosheet Films. <i>Advanced Functional Materials</i> , 2018 , 28, 1705908	15.6	77
268	Origin of the β -shaped temperature dependence of luminescent peaks from semiconductors. <i>Journal of Physics Condensed Matter</i> , 2005 , 17, 4853-4858	1.8	75
267	Dynamic Control of Double Plasmon-Induced Transparencies in Aperture-Coupled Waveguide-Cavity System. <i>Plasmonics</i> , 2018 , 13, 345-352	2.4	74
266	Zinc oxide ribbon and comb structures: synthesis and optical properties. <i>Chemical Physics Letters</i> , 2004 , 394, 452-457	2.5	74
265	Room-temperature continuous-wave electrically pumped InGaN/GaN quantum well blue laser diode directly grown on Si. <i>Light: Science and Applications</i> , 2018 , 7, 13	16.7	73
264	Photoluminescence and electroluminescence from copper doped zinc sulphide nanocrystals/polymer composite. <i>Applied Physics Letters</i> , 1998 , 73, 2727-2729	3.4	73
263	Quantum dot vertical-cavity surface-emitting lasers covering the 'green gap'. <i>Light: Science and Applications</i> , 2017 , 6, e16199	16.7	70
262	An Indoor Broadband Broadcasting System Based on PLC and VLC. <i>IEEE Transactions on Broadcasting</i> , 2015 , 61, 299-308	4.7	70
261	Efficient multiphoton-absorption-induced luminescence in single-crystalline ZnO at room temperature. <i>Optics Letters</i> , 2005 , 30, 3377-9	3	69
260	Role of edge dislocations in enhancing the yellow luminescence of n-type GaN. <i>Applied Physics Letters</i> , 2006 , 88, 241917	3.4	69
259	Green luminescence band in ZnO: fine structures, electron-phonon coupling, and temperature effect. <i>Journal of Physical Chemistry B</i> , 2006 , 110, 10475-8	3.4	68
258	Effect of temperature on longitudinal optical phonon-assisted exciton luminescence in heteroepitaxial GaN layer. <i>Applied Physics Letters</i> , 2000 , 77, 3376-3378	3.4	65
257	Detection of a superconducting phase in a two-atom layer of hexagonal Ga film grown on semiconducting GaN(0001). <i>Physical Review Letters</i> , 2015 , 114, 107003	7.4	64
256	Magnetite (Fe ₃ O ₄) tetrakaidecahedral microcrystals: Synthesis, characterization, and micro-Raman study. <i>Materials Characterization</i> , 2011 , 62, 148-151	3.9	63
255	A generalized model for time-resolved luminescence of localized carriers and applications: Dispersive thermodynamics of localized carriers. <i>Scientific Reports</i> , 2017 , 7, 13	4.9	62
254	Normally OFF GaN-on-Si MIS-HEMTs Fabricated With LPCVD-SiN _x Passivation and High-Temperature Gate Recess. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 614-619	2.9	60
253	Time-resolved photoluminescence spectra of strong visible light-emitting SiC nanocrystalline films on Si deposited by electron-cyclotron-resonance chemical-vapor deposition. <i>Applied Physics Letters</i> , 2000 , 76, 2550-2552	3.4	59

252	A set of manganese ion activated fluoride phosphors (A ₂ BF ₆ :Mn ⁴⁺ , A = K, Na, B = Si, Ge, Ti): synthesis below 0 °C and efficient room-temperature photoluminescence. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 9561-9568	7.1	57
251	Tunable and high-sensitivity sensing based on Fano resonance with coupled plasmonic cavities. <i>Scientific Reports</i> , 2017 , 7, 10639	4.9	53
250	Improved Performance of Spherical BaWO ₄ :Tb ³⁺ Phosphors for Field-Emission Displays. <i>Journal of the Electrochemical Society</i> , 2009 , 156, J112	3.9	51
249	Fabrication of pH-responsive PLGA(UCNPs/DOX) nanocapsules with upconversion luminescence for drug delivery. <i>Scientific Reports</i> , 2017 , 7, 18014	4.9	47
248	Direct determination of free exciton binding energy from phonon-assisted luminescence spectra in GaN epilayers. <i>Applied Physics Letters</i> , 2002 , 81, 2959-2961	3.4	44
247	Self-adaptive electronic contact between graphene and semiconductors. <i>Applied Physics Letters</i> , 2012 , 100, 122108	3.4	42
246	Branched Luminescent Multinuclear Platinum(II) Alkynyl Complexes: Candidates for Efficient Two-Photon Induced Luminescence. <i>Organometallics</i> , 2008 , 27, 5453-5458	3.8	39
245	Photoluminescence and photoconductivity properties of copper-doped Cd _{1-x} Zn _x S nanoribbons. <i>Nanotechnology</i> , 2006 , 17, 5935-5940	3.4	38
244	Hydrothermal synthesis and luminescent properties of BaTiF ₆ :Mn ⁴⁺ red phosphor for LED backlighting. <i>Materials Research Bulletin</i> , 2016 , 73, 14-20	5.1	37
243	Widely tunable intersubband energy spacing of self-assembled InAs/GaAs quantum dots due to interface intermixing. <i>Journal of Applied Physics</i> , 1999 , 86, 2687-2690	2.5	37
242	Role of edge dislocation and Si impurity in linking the blue luminescence and yellow luminescence in n-type GaN films. <i>Applied Physics Letters</i> , 2009 , 95, 041901	3.4	36
241	Hydrogenated nanocrystalline silicon carbide films synthesized by ECR-CVD and its intense visible photoluminescence at room temperature. <i>Thin Solid Films</i> , 2000 , 377-378, 177-181	2.2	35
240	X-ray diffraction and optical characterization of interdiffusion in self-assembled InAs/GaAs quantum-dot superlattices. <i>Applied Physics Letters</i> , 2000 , 77, 2130-2132	3.4	34
239	Vertical self-alignment of quantum dots in superlattice. <i>Applied Physics Letters</i> , 1999 , 74, 1809-1811	3.4	34
238	Photoluminescence and Raman mapping characterization of WS ₂ monolayers prepared using top-down and bottom-up methods. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 2589-2592	7.1	33
237	418cm ⁻¹ Raman scattering from gallium nitride nanowires: Is it a vibration mode of N-rich GaN bond configuration?. <i>Applied Physics Letters</i> , 2007 , 91, 103117	3.4	33
236	Room-Temperature Electrically Injected AlGaIn-Based near-Ultraviolet Laser Grown on Si. <i>ACS Photonics</i> , 2018 , 5, 699-704	6.3	31
235	Anomalous Temperature-Dependent Exciton-Phonon Coupling in Cesium Lead Bromide Perovskite Nanosheets. <i>Journal of Physical Chemistry C</i> , 2019 , 123, 5128-5135	3.8	30

234	Micro-Raman and photoluminescence studies of neutron-irradiated gallium nitride epilayers. <i>Applied Physics Letters</i> , 2005 , 87, 031906	3.4	29
233	p-GaN Gate Enhancement-Mode HEMT Through a High Tolerance Self-Terminated Etching Process. <i>IEEE Journal of the Electron Devices Society</i> , 2017 , 5, 340-346	2.3	28
232	On-wafer fabrication of cavity mirrors for InGaN-based laser diode grown on Si. <i>Scientific Reports</i> , 2018 , 8, 7922	4.9	28
231	Carrier Localization Effects in InGaN/GaN Multiple-Quantum-Wells LED Nanowires: Luminescence Quantum Efficiency Improvement and "Negative" Thermal Activation Energy. <i>Scientific Reports</i> , 2016 , 6, 34545	4.9	27
230	Light-splitting photovoltaic system utilizing two dual-junction solar cells. <i>Solar Energy</i> , 2010 , 84, 1975-1978		27
229	Phonon-assisted photoluminescence in wurtzite GaN epilayer. <i>Semiconductor Science and Technology</i> , 1998 , 13, 769-772	1.8	27
228	Polarization dependence of intraband absorption in self-organized quantum dots. <i>Applied Physics Letters</i> , 1998 , 73, 1997-1999	3.4	27
227	Silica capping for Al _{0.3} Ga _{0.7} As/GaAs and In _{0.2} Ga _{0.8} As/GaAs quantum well intermixing. <i>Applied Physics Letters</i> , 1998 , 73, 3393-3395	3.4	27
226	Integrated power line and visible light communication system compatible with multi-service transmission. <i>IET Communications</i> , 2017 , 11, 104-111	1.3	26
225	Polarization-dependent supercontinuum generation from light filaments in air. <i>Optics Letters</i> , 2005 , 30, 534-6	3	26
224	Comparative study on the broadening of exciton luminescence linewidth due to phonon in zinc-blende and wurtzite GaN epilayers. <i>Applied Physics Letters</i> , 2002 , 81, 4389-4391	3.4	26
223	Quantum dissipation and broadening mechanisms due to electron-phonon interactions in self-formed InGaN quantum dots. <i>Applied Physics Letters</i> , 2006 , 88, 083123	3.4	25
222	Resonant coupling of bound excitons with LO phonons in ZnO: excitonic polaron states and Fano interference. <i>Journal of Chemical Physics</i> , 2005 , 123, 221105	3.9	25
221	Impact of the cap layer on the electronic structures and optical properties of self-assembled InAs/GaAs quantum dots. <i>Physical Review B</i> , 2006 , 74,	3.3	25
220	Room-temperature continuous-wave operation of GaN-based blue-violet laser diodes with a lifetime longer than 1000 h. <i>Journal of Semiconductors</i> , 2019 , 40, 022801	2.3	24
219	Understanding and manipulating luminescence in carbon nanodots. <i>Carbon</i> , 2018 , 126, 58-64	10.4	24
218	Large Negative-Thermal-Quenching Effect in Phonon-Induced Light Emissions in Mn-Activated Fluoride Phosphor for Warm-White Light-Emitting Diodes. <i>ACS Omega</i> , 2018 , 3, 13704-13710	3.9	24
217	Thermal quenching of luminescence from buried and surface InGaAs self-assembled quantum dots with high sheet density. <i>Journal of Applied Physics</i> , 2005 , 98, 084305	2.5	23

216	High-performance UV detectors based on room-temperature deposited amorphous Ga ₂ O ₃ thin films by RF magnetron sputtering. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 11834-11844	7.1	22
215	Indoor hospital communication systems: An integrated solution based on power line and visible light communication 2014 ,		22
214	Temperature dependence of the LO phonon sidebands in free exciton emission of GaN. <i>Journal of Applied Physics</i> , 2006 , 99, 073508	2.5	22
213	Mechanism of Single-Photon Upconversion Photoluminescence in All-Inorganic Perovskite Nanocrystals: The Role of Self-Trapped Excitons. <i>Journal of Physical Chemistry Letters</i> , 2019 , 10, 5989-5996	6.4	21
212	Photoinduced doping and photoluminescence signature in an exfoliated WS ₂ monolayer semiconductor. <i>RSC Advances</i> , 2016 , 6, 27677-27681	3.7	21
211	Electron g-factor distribution in self-assembled quantum dots. <i>Physical Review B</i> , 2008 , 77,	3.3	21
210	Excitation Dependent Phosphorous Property and New Model of the Structured Green Luminescence in ZnO. <i>Scientific Reports</i> , 2017 , 7, 41460	4.9	20
209	Substrate effects on quasiparticles and excitons in graphene nanoflakes. <i>Applied Physics Letters</i> , 2013 , 103, 143109	3.4	20
208	Optical characterization of structure for semiconductor quantum dots. <i>Physical Review B</i> , 2008 , 77,	3.3	20
207	Temperature and pressure behavior of the emission bands from Mn-, Cu-, and Eu-doped ZnS nanocrystals. <i>Journal of Applied Physics</i> , 2004 , 95, 3344-3349	2.5	20
206	Nature of red luminescence band in research-grade ZnO single crystals: A self-activated [□] configurational transition. <i>Applied Physics Letters</i> , 2014 , 105, 041912	3.4	19
205	Effects of annealing temperature on the characteristics of Ga-doped ZnO film metal-semiconductor-metal ultraviolet photodetectors. <i>Journal of Applied Physics</i> , 2013 , 113, 084501	2.5	19
204	Evidence for a Type-II band alignment between cubic and hexagonal phases of GaN. <i>Applied Physics Letters</i> , 2003 , 82, 1033-1035	3.4	19
203	GaN-Based Blue Laser Diodes With 2.2 W of Light Output Power Under Continuous-Wave Operation. <i>IEEE Photonics Technology Letters</i> , 2017 , 29, 2203-2206	2.2	18
202	Localized surface optical phonon mode in the InGaN/GaN multiple-quantum-wells nanopillars: Raman spectrum and imaging. <i>Applied Physics Letters</i> , 2011 , 99, 113115	3.4	18
201	Classification of bound exciton complexes in bulk ZnO by magnetophotoluminescence spectroscopy. <i>Journal of Applied Physics</i> , 2009 , 105, 053511	2.5	18
200	Influence of defects in nGaN layer on the responsivity of Schottky barrier ultraviolet photodetectors. <i>Applied Physics Letters</i> , 2007 , 90, 062106	3.4	18
199	Observation of both second-harmonic and multiphoton-absorption-induced luminescence in ZnO. <i>IEEE Photonics Technology Letters</i> , 2006 , 18, 1533-1535	2.2	18

198	Broadband Spin-Driven Anomalous Surface Plasmon Polariton Steering via V-Shaped Aperture Metasurfaces. <i>Advanced Theory and Simulations</i> , 2019 , 2, 1800167	3.5	18
197	Electric field driven magnetic phase transition in graphene nanoflakes. <i>Applied Physics Letters</i> , 2013 , 103, 133103	3.4	17
196	A practical route towards fabricating GaN nanowire arrays. <i>CrystEngComm</i> , 2011 , 13, 5929	3.3	17
195	Probing deep level centers in GaN epilayers with variable-frequency capacitance-voltage characteristics of Au/GaN Schottky contacts. <i>Applied Physics Letters</i> , 2006 , 89, 143505	3.4	17
194	Luminescence signature of free exciton dissociation and liberated electron transfer across the junction of graphene/GaN hybrid structure. <i>Scientific Reports</i> , 2015 , 5, 7687	4.9	16
193	Photoluminescence signatures of thermal expansion, electron-phonon coupling and phase transitions in cesium lead bromide perovskite nanosheets. <i>Nanoscale</i> , 2020 , 12, 7315-7320	7.7	16
192	Effective recombination velocity of textured surfaces. <i>Applied Physics Letters</i> , 2010 , 96, 193107	3.4	16
191	Spectral features of LO phonon sidebands in luminescence of free excitons in GaN. <i>Journal of Chemical Physics</i> , 2005 , 122, 244712	3.9	16
190	Tris(8-hydroxyquinoline) aluminium nanowires: a simple synthesis method. <i>Chemical Physics Letters</i> , 2004 , 394, 203-206	2.5	16
189	Interpretation of anomalous temperature dependence of anti-Stokes photoluminescence at GaInP2/GaAs interface. <i>Applied Physics Letters</i> , 2004 , 84, 2280-2282	3.4	16
188	Shallow optically active structural defect in wurtzite GaN epilayers grown on stepped 4H-SiC substrates. <i>Applied Physics Letters</i> , 2003 , 83, 3477-3479	3.4	16
187	Film thickness degradation of Au/GaN Schottky contact characteristics. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005 , 117, 21-25	3.1	16
186	Reflective metalens with sub-diffraction-limited and multifunctional focusing. <i>Scientific Reports</i> , 2017 , 7, 12632	4.9	15
185	Luminescence landscapes of nitrogen-vacancy centers in diamond: quasi-localized vibrational resonances and selective coupling. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 8086-8091	7.1	15
184	One-Pot Synthesis of Carboxyl-Functionalized Rare Earth Fluoride Nanocrystals with Monodispersity, Ultrasmall Size and Very Bright Luminescence. <i>European Journal of Inorganic Chemistry</i> , 2011 , 2011, 2158-2163	2.3	15
183	Triplet harvesting in luminescent Cu(I) complexes by the thermally activated luminescence transition mechanism: impact of the molecular structure. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 4488-4494	7.1	14
182	Raman scattering studies of dilute InP1-xBi alloys reveal unusually strong oscillator strength for Bi-induced modes. <i>Semiconductor Science and Technology</i> , 2015 , 30, 094003	1.8	14
181	Sub-Wavelength Grating Enhanced Ultra-Narrow Graphene Perfect Absorber. <i>Plasmonics</i> , 2018 , 13, 2267-2272	7.2	14

180	Transition of radiative recombination channels from delocalized states to localized states in a GaInP alloy with partial atomic ordering: a direct optical signature of Mott transition?. <i>Nanoscale</i> , 2016 , 8, 7113-8	7.7	14
179	Key Technologies and Measurements for DTMB-A System. <i>IEEE Transactions on Broadcasting</i> , 2019 , 65, 53-64	4.7	14
178	Design Considerations for GaN-Based Blue Laser Diodes With InGaN Upper Waveguide Layer. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2013 , 19, 1500705-1500705	3.8	14
177	Two-photon photoluminescence and excitation spectra of InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , 2006 , 89, 011104	3.4	14
176	Photoluminescence of doped ZnS nanoparticles under hydrostatic pressure. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 3248-3256	1.3	14
175	Structural dependences of localization and recombination of photogenerated carriers in the top GaInP Subcells of GaInP/GaAs double-junction tandem solar cells. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 690-5	9.5	13
174	Significant increase of quantum efficiency of green InGaN quantum well by realizing step-flow growth. <i>Applied Physics Letters</i> , 2017 , 111, 112102	3.4	13
173	Effect of localization states on the electroluminescence spectral width of blue-green light emitting InGaN/GaN multiple quantum wells. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 061502	2.9	13
172	Unintentionally doped semi-insulating GaN with a low dislocation density grown by metalorganic chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 051207	1.3	13
171	Determination of effective mass of heavy hole from phonon-assisted excitonic luminescence spectra in ZnO. <i>Journal of Applied Physics</i> , 2011 , 109, 053510	2.5	13
170	Strong influence of SiO ₂ thin film on properties of GaN epilayers. <i>Applied Physics Letters</i> , 1999 , 74, 818-820	3.4	13
169	Design and growth of GaN-based blue and green laser diodes. <i>Science China Materials</i> , 2020 , 63, 1348-1363	3.3	13
168	Reduction of Polarization Field Strength in Fully Strained c-Plane InGaN/(In)GaN Multiple Quantum Wells Grown by MOCVD. <i>Nanoscale Research Letters</i> , 2016 , 11, 519	5	13
167	The effect of Ga-doped nanocrystalline ZnO electrode on deep-ultraviolet enhanced GaN photodetector. <i>Applied Physics Letters</i> , 2013 , 102, 212104	3.4	12
166	Influence of aspect ratio on tumbling plates. <i>Journal of Fluid Mechanics</i> , 2013 , 733, 650-679	3.7	12
165	Electron irradiation study of room-temperature wafer-bonded four-junction solar cell grown by MBE. <i>Solar Energy Materials and Solar Cells</i> , 2017 , 171, 118-122	6.4	12
164	Broadband second harmonic generation from ZnO nano-tetrapods. <i>Chemical Physics Letters</i> , 2011 , 506, 226-229	2.5	12
163	Influence of capping layer and atomic interdiffusion on the strain distribution in single and double self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , 2008 , 92, 083112	3.4	12

162	. <i>IEEE Photonics Technology Letters</i> , 2007 , 19, 789-791	2.2	12
161	Band gap renormalization and carrier localization effects in InGaN/GaN quantum-wells light emitting diodes with Si doped barriers. <i>Applied Physics Letters</i> , 2006 , 88, 041903	3.4	12
160	Theoretical absorption spectra of silicon carbide nanocrystals. <i>Thin Solid Films</i> , 2006 , 495, 404-406	2.2	12
159	The depth-profiled carrier concentration and scattering mechanism in undoped GaN film grown on sapphire. <i>Journal of Applied Physics</i> , 2004 , 96, 1120-1126	2.5	12
158	Blueshift of effective band gap in n-i-p-i doping superlattices as a function of optical excitation intensity. <i>Journal of Applied Physics</i> , 1998 , 83, 1476-1480	2.5	12
157	Stable, High-Efficiency Voltage-Dependent Color-Tunable Organic Light-Emitting Diodes with a Single Tetradentate Platinum(II) Emitter Having Long Operational Lifetime. <i>Advanced Materials</i> , 2021 , 33, e2004873	24	12
156	Boosting phonon-induced luminescence in red fluoride phosphors via composition-driven structural transformations. <i>Journal of Materials Chemistry C</i> , 2017 , 5, 12105-12111	7.1	11
155	Polarized and non-polarized photoluminescence of GaInP2 alloy with partial CuPt-type atomic ordering: ordered domains vs. disordered regions. <i>Journal of Materials Chemistry C</i> , 2014 , 2, 6119-6124	7.1	11
154	Two-electron-satellite transition of donor bound exciton in ZnO: Radiative Auger effect. <i>Applied Physics Letters</i> , 2013 , 102, 181909	3.4	11
153	Radiative recombination of carriers in the GaInN/P/GaAs double-junction tandem solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2013 , 111, 102-106	6.4	11
152	Luminescence Anisotropy and Thermal Effect of Magnetic and Electric Dipole Transitions of Cr Ions in Yb:YAG Transparent Ceramic. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 43790-43798	9.5	11
151	Influence of indium-tin-oxide thin-film quality on reverse leakage current of indium-tin-oxide/n-GaN Schottky contacts. <i>Applied Physics Letters</i> , 2006 , 89, 033503	3.4	11
150	Effect of lightly Si doping on the minority carrier diffusion length in n-type GaN films. <i>Applied Physics Letters</i> , 2006 , 88, 252101	3.4	11
149	Strong interaction of Fermi-edge singularity and exciton related to N=2 subband in a modulation-doped Al _x Ga _{1-x} As/In _y Ga _{1-y} As/GaAs quantum well. <i>Physical Review B</i> , 1996 , 54, 17701-17704	2.3	11
148	Extinction of the zero-phonon line and the first-order phonon sideband in excitonic luminescence of ZnO at room temperature: the self-absorption effect. <i>Science Bulletin</i> , 2017 , 62, 1525-1529	10.6	10
147	Strong quantum confinement effect and reduced Fröhlich exciton-phonon coupling in ZnO quantum dots embedded inside a SiO ₂ matrix. <i>Nanoscale</i> , 2015 , 7, 17482-7	7.7	10
146	Tunable positive magnetoresistance effect of Co-doped amorphous carbon films. <i>Journal of Applied Physics</i> , 2012 , 111, 07C510	2.5	10
145	Sequential resonant tunnelling through Landau levels in GaAs/AlAs superlattices. <i>Semiconductor Science and Technology</i> , 1997 , 12, 1422-1424	1.8	10

144	Investigation of dislocations and traps in MBE grown p-InGaAs/GaAs heterostructures. <i>Thin Solid Films</i> , 1997 , 311, 7-14	2.2	10
143	Resonantly enhanced femtosecond second-harmonic generation and nonlinear luminescence in GaN film grown on sapphire. <i>Applied Physics Letters</i> , 2006 , 88, 161113	3.4	10
142	Determination of carbon-related trap energy level in (Al)GaN buffers for high electron mobility transistors through a room-temperature approach. <i>Applied Physics Letters</i> , 2020 , 117, 263501	3.4	10
141	Precise determination of surface band bending in Ga-polar n-GaN films by angular dependent X-Ray photoemission spectroscopy. <i>Scientific Reports</i> , 2019 , 9, 16969	4.9	10
140	A real-time high-speed visible light communication system based on RGB-LEDs 2017 ,		9
139	Effects of Fe doping on the strain and optical properties of GaN epilayers grown on sapphire substrates. <i>RSC Advances</i> , 2014 , 4, 55430-55434	3.7	9
138	Impurity scattering induced excitonic polariton damping and its influence on the reflectance spectra of GaN epilayers. <i>Journal of Applied Physics</i> , 2009 , 106, 013514	2.5	9
137	Spontaneous emission mechanisms of GaInAsN/GaAs quantum dot systems. <i>Journal of Applied Physics</i> , 2006 , 100, 124311	2.5	9
136	Green laser diodes with low operation voltage obtained by suppressing carbon impurity in AlGaIn: Mg cladding layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 245-247		9
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